



JOCT101X-L4 Series

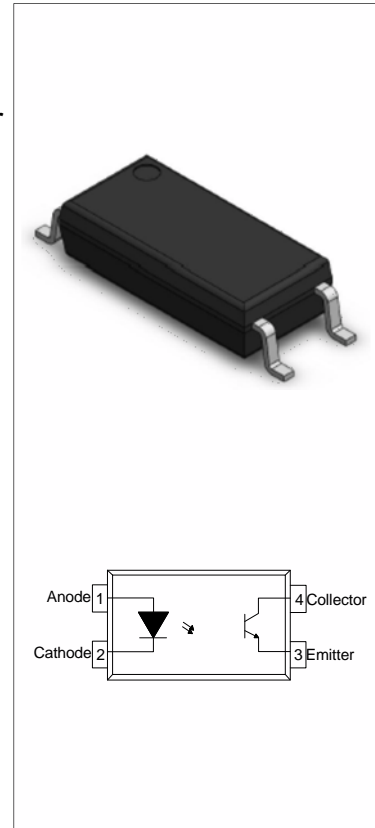
Rev.A.1.0

DESCRIPTION:

The products are transistor opto-couplers in a plastic LSOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances, office equipment, etc.

MAIN FEATURES

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range -55°C to 110°C
- RoHS & REACH Compliance
- HBM: H3A ; MM: M4; CDM:C3
- CQC approved
- VDE approved
- UL approved



ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	7	V
	Collector Current	I_C	50	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	2	mW
Isolation Voltage		V_{iso}	5000	Vrms
Operating Temperature		T_{opr}	-55~+110	
Junction Temperature		T_j	125	

Storage Temperature	T _{stg}	-55~+125	
Soldering Temperature	T _{sol}	260	

NOTE1: μ

NOTE2

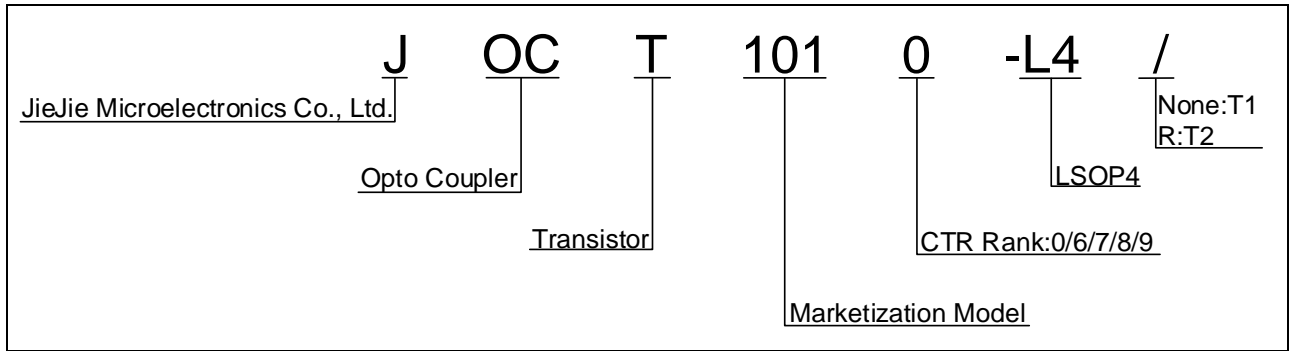
ELECTRICAL CHARACTERISTICS (Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V _F	I _F =10mA	-	1.2	1.5	V
	Reverse Current	I _R	V _R =6V	-	-	1	μ A
	Terminal Capacitance	C _t	V=0, f=1MHz	-	30	250	pF
Output	Collector-Emitter dark current	I _{CEO}	V _{CE} =20V, I _F =0	-	-	50	nA
	Collector-Emitter breakdown voltage	BV _{CEO}	I _C =0.1mA I _F =0	80	-	-	V
	Emitter-Collector breakdown voltage	BV _{ECO}	I _E =0.1mA I _F =0	7	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	I _F =5mA V _{CE} =5V	80	-	600	%
	Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _F =10mA I _C =1mA	-	0.1	0.2	V
	Isolation resistance	R _{IO}	DC500V 40~60%R.H.	5x10 ¹⁰	-	-	
	Floating Capacitance	C _{IO}	V=0, f=1MHz	-	0.6	1	pF
	Cut-off Frequency	f _c	V _{CE} =5V, I _C =2mA R _L =100 Ω , -3dB	-	80	-	kHz
	Rise Time	t _r	V _{CE} =2V, I _C =2mA R _L =100 Ω	-	4	18	μ s
	Fall Time	t _f		-	5	18	μ s
	Turn On Time	t _{on}		-	8	25	μ s
Turn Off Time	t _{off}	-		5	25	μ s	

NOTE1:

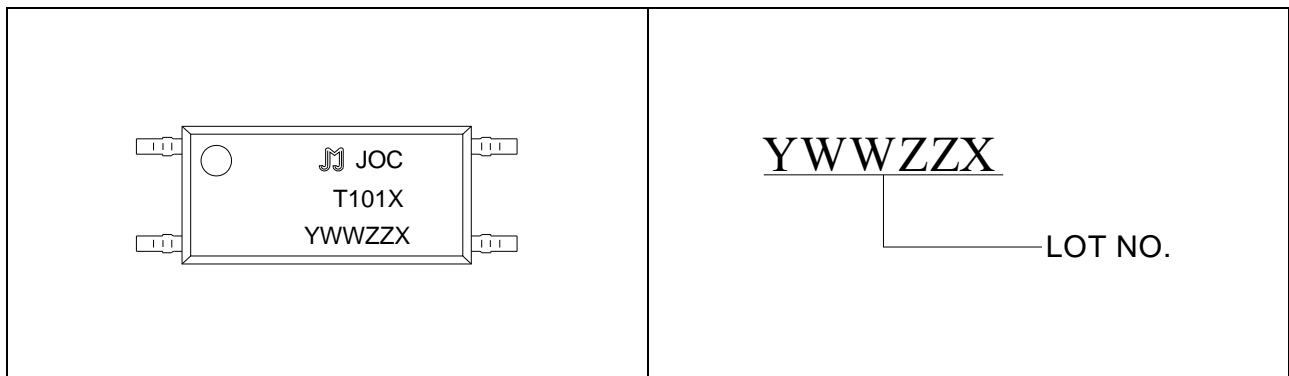
CTR Rank	Min. (%)	Max. (%)
JOCT1010	300	600
JOCT1016	100	300
JOCT1017	80	160
JOCT1018	130	260
JOCT1019	200	400

ORDERING INFORMATION



Packing Quantity	
Option	Quantity

MARKING



Characteristics Curves

FIG.1: Max. Allowable LED Forward Current vs. Ambient Temperature

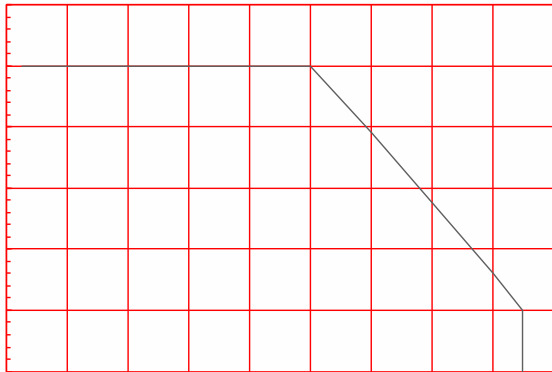


FIG.2: Collector Power Dissipation vs. Ambient Temperature

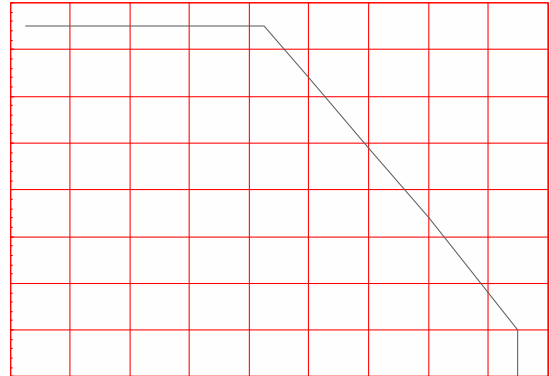


FIG.3: Forward Current vs. Forward Voltage

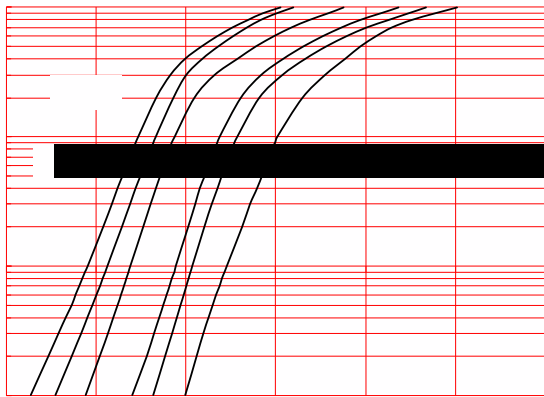


FIG.4: Normalized Collector Dark Current vs. Ambient Temperature

FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

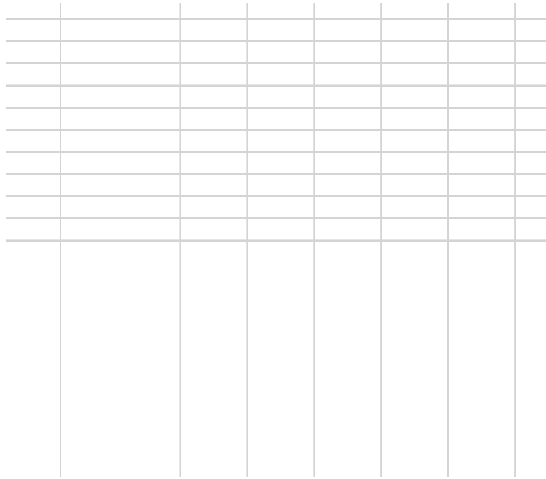


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

Test Circuits

FIG.11: Test Circuits of Response Time

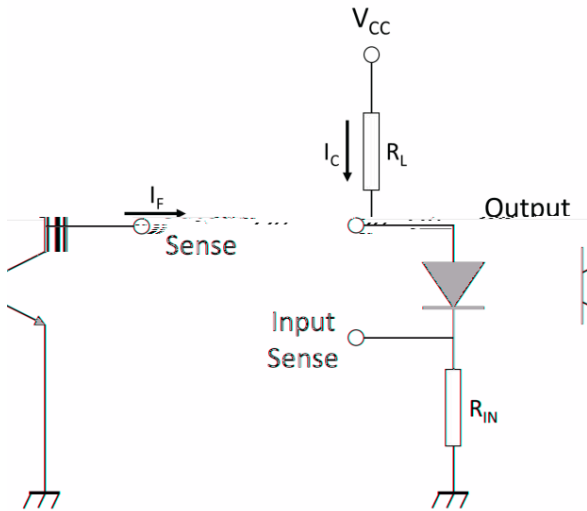


FIG.12: Curves of Response Time

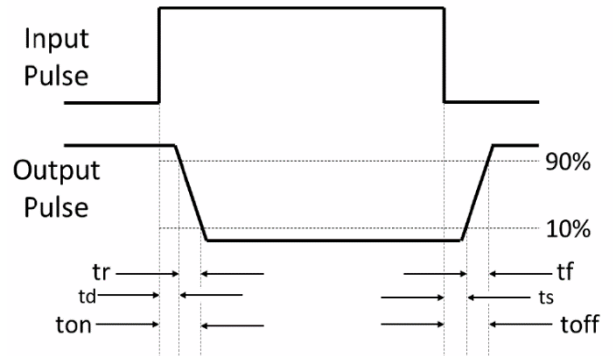
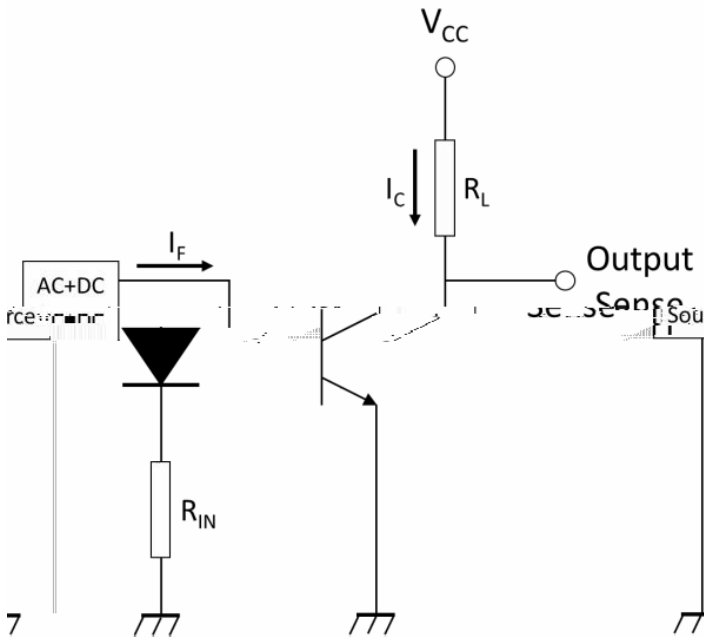
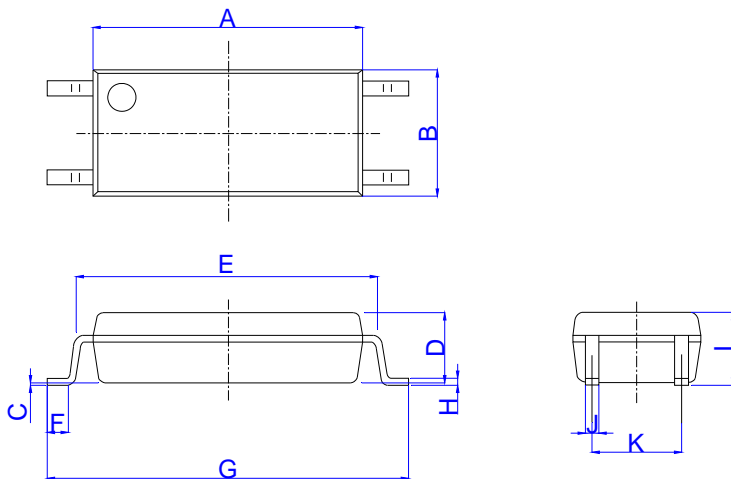


FIG.13: Test Circuits of Frequency Response

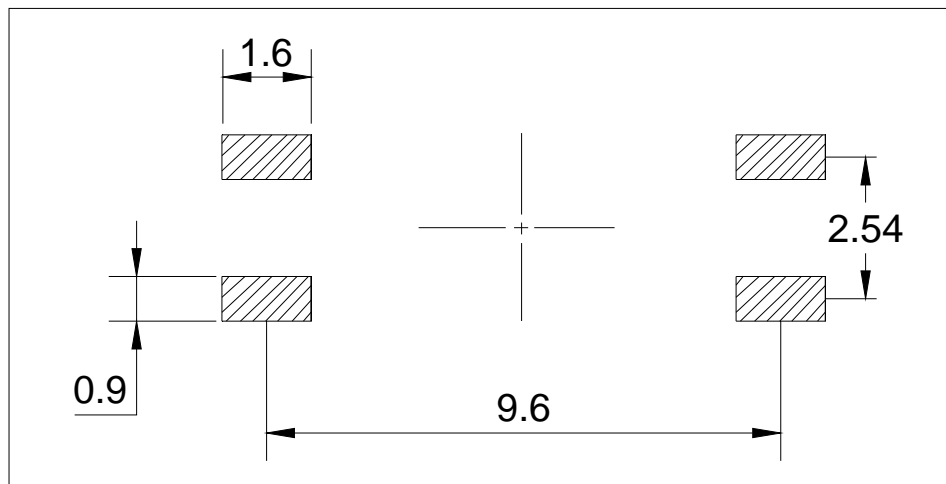


Package Dimension (Unit: mm)



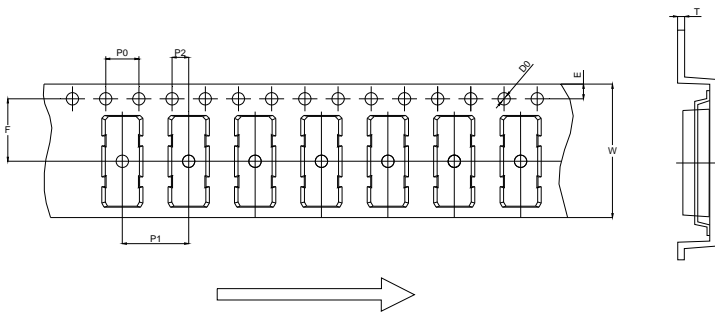
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	3.40		3.80	0.134		0.150
C	0.00		0.20	0.000		0.008
D	1.80		2.20	0.071		0.087
E	8.10		8.70	0.319		0.343
F	0.40		1.00	0.016		0.039
G	9.90		10.50	0.390		0.413
H	0.10		0.30	0.004		0.012
I	1.80		2.40	0.071		0.094
J	0.25		0.55	0.010		0.022
K	2.29		2.79	0.090		0.110

RECOMMENDED SOLDER MASK (Dimensions in mm unless otherwise stated)



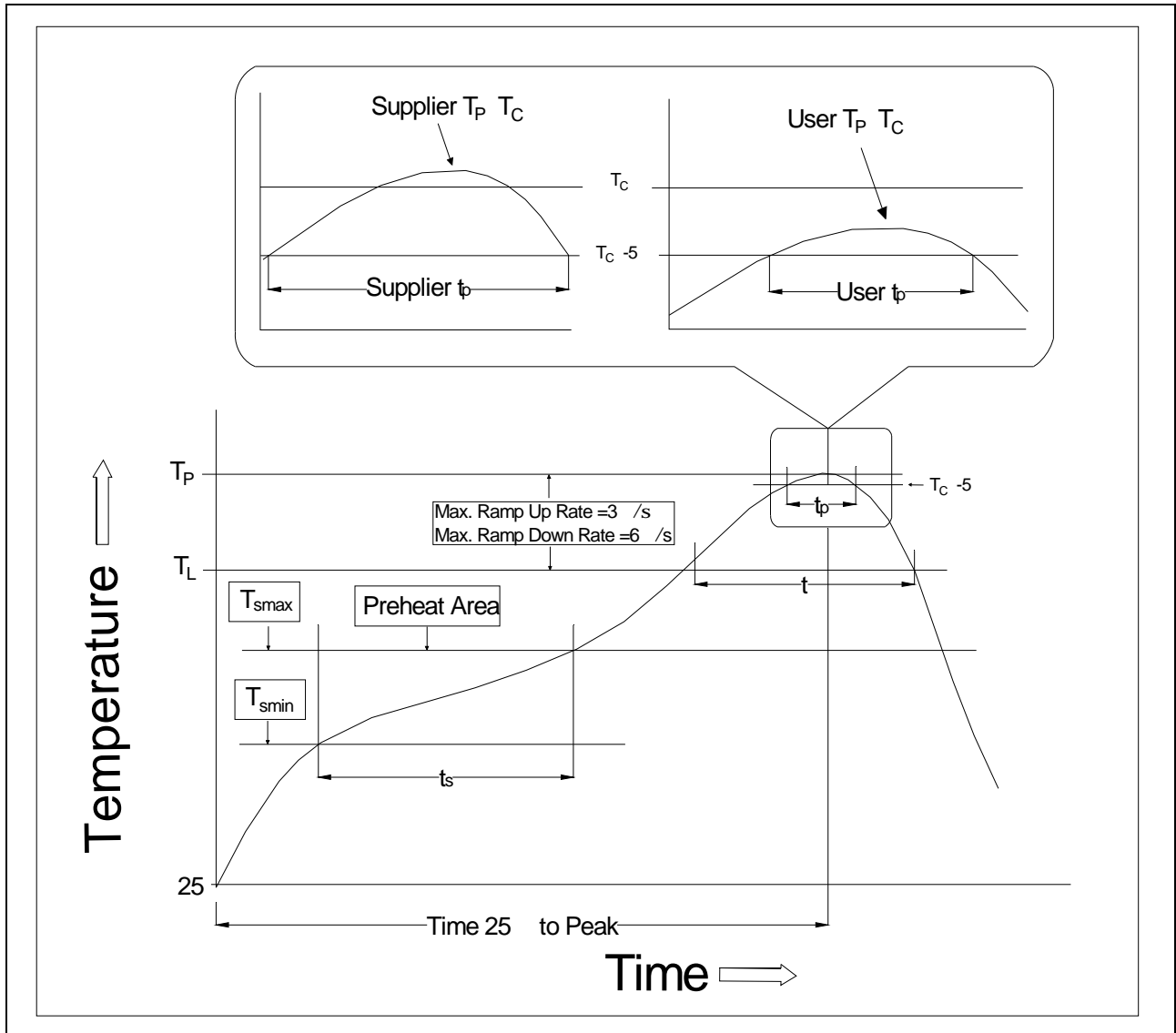
CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option None/R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0	1.50	1.55	1.60	0.059	0.061	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.35	0.40	0.45	0.014	0.016	0.018
W	15.80	16.00	16.20	0.622	0.630	0.638

REFLOW INFORMATION



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T _{min})	100	150
Temperature Max. (T _{smax})	150	200
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t _L to t _P)	3 °C/second max.	3 °C/second max.
Liquidus Temperature (T _L)	183	217
Time (t _L) Maintained Above (T _L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time (t _P) within 5 °C of 260	20 seconds	30 seconds
Ramp-down Rate (T _P to T _L)	6 °C/second max.	6 °C/second max.
Time 25 °C to Peak Temperature	6 minutes max.	8 minutes max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf lif